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**SiC**

Silicon Carbide Diode

**5<sup>th</sup> Generation thinQ!<sup>TM</sup>**

650V SiC Schottky Diode

**IDL08G65C5**

**Final Data Sheet**

Rev2.1, 2016-04-19

**Power Management & Multimarket**

## 5<sup>th</sup> Generation thinQ!™ SiC Schottky Diode

### 1 Description

ThinQ!™ Generation 5 represents Infineon leading edge technology for the SiC Schottky Barrier diodes. The Infineon proprietary diffusion soldering process, already introduced with G3 is now combined with a new, more compact design and thin-wafer technology. The result is a new family of products showing improved efficiency over all load conditions, resulting from both the improved thermal characteristics and a lower figure of merit ( $Q_c \times V_f$ ).

The new thinQ!™ Generation 5 has been designed to complement our 650V CoolMOS™ families: this ensures meeting the most stringent application requirements in this voltage range.

#### Features

- Revolutionary semiconductor material - Silicon Carbide
- Benchmark switching behavior
- No reverse recovery/ No forward recovery
- Temperature independent switching behavior
- High surge current capability
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC<sup>1)</sup> for target applications
- Breakdown voltage tested at 18 mA<sup>2)</sup>
- Optimized for high temperature operation

#### Benefits

- System efficiency improvement over Si diodes
- System cost / size savings due to reduced cooling requirements
- Enabling higher frequency / increased power density solutions
- Higher system reliability due to lower operating temperatures
- Reduced EMI

#### Applications

- Switch mode power supply
- Power factor correction
- Solar inverter
- Uninterruptible power supply

**Table 1 Key Performance Parameters**

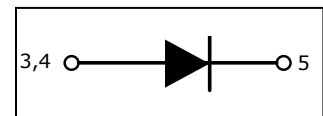
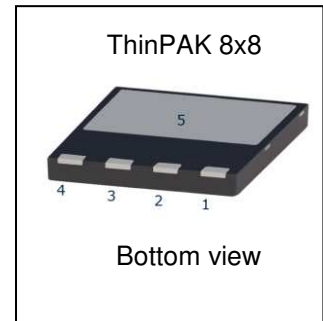
Parameter	Value	Unit
$V_{DC}$	650	V
$Q_C; V_R=400V$	13	nC
$E_C; V_R=400V$	2.9	μJ
$I_F @ T_C < 150^\circ C$	8	A

**Table 2 Pin Definition**

Pin 1	Pin 2	Pin 3	Pin 4	Pin 5
n.c.	n.c.	A	A	C

Type / ordering Code	Package	Marking
IDL08G65C5	PG-VSON-4	D0865C5

### IDL08G65C5



#### Related Links

- <http://www.infineon.com/sic>
- [ThinPAK Webpage](#)
- [ThinPAK Application Note](#)

1) J-STD20 and JEDEC22

2) All devices tested under avalanche conditions for a time period of 10ms

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## 2 Maximum ratings

**Table 3** Maximum ratings

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Continuous forward current	$I_F$	–	–	8	A	$T_C < 125^\circ\text{C}$ , $D=1$
Surge non-repetitive forward current, sine halfwave	$I_{F,SM}$	–	–	43		$T_C = 25^\circ\text{C}$ , $t_p=10\text{ ms}$
		–	–	36		$T_C = 150^\circ\text{C}$ , $t_p=10\text{ ms}$
Non-repetitive peak forward current	$I_{F,max}$	–	–	364		$T_C = 25^\circ\text{C}$ , $t_p=10\ \mu\text{s}$
$i^2t$ value	$\int i^2 dt$	–	–	9.5	A <sup>2</sup> s	$T_C = 25^\circ\text{C}$ , $t_p=10\text{ ms}$
		–	–	6.4		$T_C = 150^\circ\text{C}$ , $t_p=10\text{ ms}$
Repetitive peak reverse voltage	$V_{RRM}$	–	–	650	V	$T_j = 25^\circ\text{C}$
Diode dv/dt ruggedness	$dv/dt$	–	–	100	V/ns	$V_R=0..480\text{ V}$
Power dissipation	$P_{tot}$	–	–	96	W	$T_C = 25^\circ\text{C}$
Operating and storage temperature	$T_j; T_{stg}$	-55	–	150	°C	

## 3 Thermal characteristics

**Table 4** Thermal characteristics

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction-case	$R_{thJC}$	–	1.0	1.3	K/W	SMD version, device on PCB, 6cm <sup>2</sup> cooling area <sup>1)</sup>
Thermal resistance, junction-ambient	$R_{thJA}$	–	–	45		

1) Device on 40mm\*40mm\*1.5mm one layer epoxy PCB FR4 with 6cm<sup>2</sup> copper area (thickness 70µm) for drain connection. PCB is vertical without air stream cooling.

## 4 Electrical characteristics

**Table 5 Static characteristics**

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
DC blocking voltage	$V_{DC}$	650	–	–	V	$I_R = 0.14 \text{ mA}, T_j = 25^\circ\text{C}$
Diode forward voltage	$V_F$	–	1.5	1.7		$I_F = 8 \text{ A}, T_j = 25^\circ\text{C}$
		–	1.8	2.1		$I_F = 8 \text{ A}, T_j = 150^\circ\text{C}$
Reverse current	$I_R$	–	0.4	140	$\mu\text{A}$	$V_R = 650 \text{ V}, T_j = 25^\circ\text{C}$
		–	0.1	50		$V_R = 600 \text{ V}, T_j = 25^\circ\text{C}$
		–	1.6	1000		$V_R = 650 \text{ V}, T_j = 150^\circ\text{C}$

**Table 6 AC characteristics**

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Total capacitive charge	$Q_c$	–	13	–	nC	$V_R = 400 \text{ V}, di/dt = 200 \text{ A}/\mu\text{s}, I_F \leq I_{F,MAX}, T_j = 150^\circ\text{C}.$
Total Capacitance	$C$	–	250	–	pF	$V_R = 1 \text{ V}, f = 1 \text{ MHz}$
		–	32	–		$V_R = 300 \text{ V}, f = 1 \text{ MHz}$
		–	32	–		$V_R = 600 \text{ V}, f = 1 \text{ MHz}$

## 5 Electrical characteristics diagrams

Table 7

Power dissipation	Maximal diode forward current
$P_{\text{tot}} = f(T_c); R_{\text{thJC,max}}$	$I_F = f(T_c); R_{\text{thJC,max}}; T_j \leq 150^\circ\text{C}; \text{parameter } D = \text{duty cycle}$

Table 8

Typical forward characteristics	Typical forward characteristics in surge current
$I_F = f(V_F); t_p = 200 \mu\text{s}; \text{parameter: } T_j$	$I_F = f(V_F); t_p = 200 \mu\text{s}; \text{parameter: } T_j$

Table 9

Typ. capacitance charge vs. current slope <sup>1)</sup>	Typ. reverse current vs. reverse voltage
$Q_C=f(dI_F/dt); T_j=150^{\circ}\text{C}; V_R=400\text{ V}; I_F \leq I_{F,\text{max}}$	$I_R=f(V_R); \text{parameter: } T_j;$

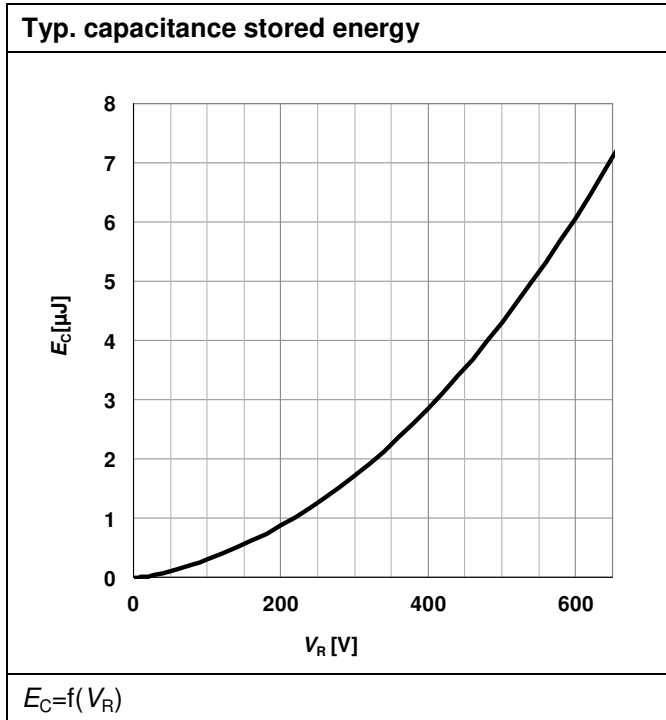
1) Only capacitive charge, guaranteed by design.

Table 10

Max. transient thermal impedance	Typ. capacitance vs. reverse voltage
$Z_{th,jc}=f(t_p); \text{parameter: } D=t_p/T$	$C=f(V_R); T_j=25^{\circ}\text{C}; f=1\text{ MHz}$



Table 11



## 6 Simplified Forward Characteristics Model

Table 12

Equivalent forward current curve	Mathematical Equation
	$V_F = V_{TH} + R_{DIFF} \cdot I_F$ $V_{TH}(T_j) = -0.001 \cdot T_j + 1.04 \text{ [V]}$ $R_{DIFF}(T_j) = 1.6 \cdot 10^{-6} \cdot T_j^2 + 1.6 \cdot 10^{-4} \cdot T_j + 0.058 \text{ [\Omega]}$
$V_F = f(I_F)$	$T_j$ in °C; $-55^\circ\text{C} < T_j < 150^\circ\text{C}$ ; $I_F < 16 \text{ A}$

7 Package outlines

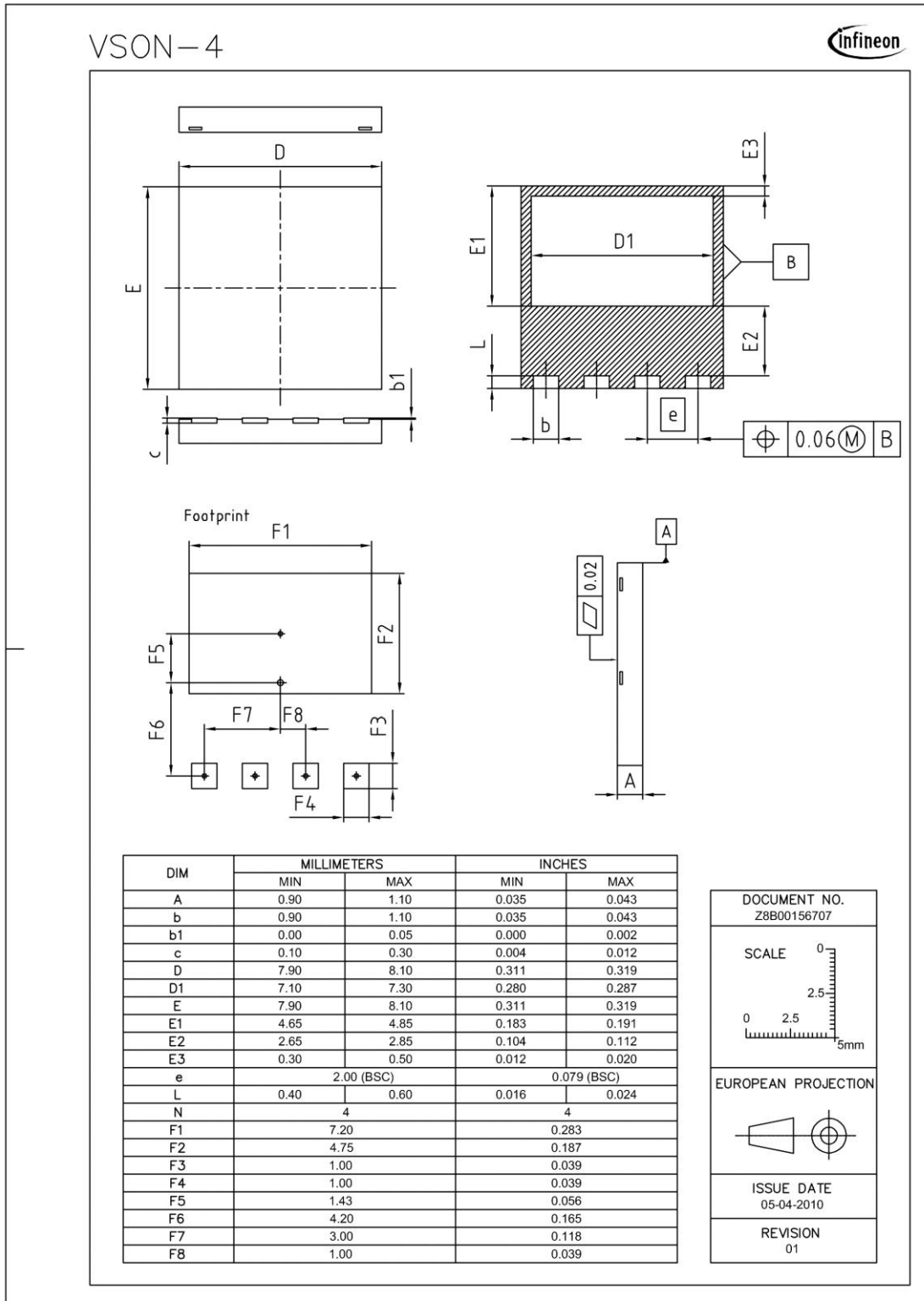


Figure 1 Outlines ThinPAK 8x8, dimensions in mm/inches

## 8 Revision History

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### 5<sup>th</sup> Generation thinQ!<sup>TM</sup> SiC Schottky Diode

Revision History: 2016-04-19, Rev. 2.1

**Previous Revision:**

Revision	Subjects (major changes since last version)
2.0	Release of the final datasheet
2.1	Correction of Test Condition Diode Forward Voltage

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Edition 2013-05-13

Published by

Infineon Technologies AG

81726 Munich, Germany

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